

ASMEX.291A



PATENT

3A
6/13/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	Todd, et al.)	Group Art Unit Unknown
Appl. No.	:	10/074,563)	
Filed	:	February 11, 2002)	I hereby certify that this correspondence and
For	:	IMPROVED PROCESS FOR)	all marked attachments are being deposited
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Examiner	:	Unknown)	<u>4/9/02</u>
)	(Date)
)	<u>Joseph J. Mallon</u>
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PRELIMINARY AMENDMENT

United States Patent and Trademark Office
P.O. Box 2327
Arlington, VA 22202

Dear Sir:

Prior to examination, please amend the above-referenced application as follows:

IN THE ABSTRACT:

Please replace the Abstract of the Disclosure with the following new Abstract:

A' Chemical vapor deposition processes utilize chemical precursors that allow for the deposition of thin films to be conducted at or near the mass transport limited regime. The processes have high deposition rates yet produce more uniform films, both compositionally and in thickness, than films prepared using conventional chemical precursors. In preferred embodiments, a higher order silane is employed to deposit thin films containing silicon that are useful in the semiconductor industry in various applications such as transistor gate electrodes.

IN THE SPECIFICATION:

Please replace paragraph [0001] with the following rewritten paragraph: